TECHNICAL DATA DATA SHEET 576, REV. A

HERMETIC POWER SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

DESCRIPTION: 45 VOLT, 30 AMP, POWER SCHOTTKY RECTIFIER IN A HERMETIC SHD-2/2B PACKAGE.

MAXIMUM RATINGS

ALL RATINGS ARE @ T_C = 25 °C UNLESS OTHERWISE SPECIFIED.

ALL RATINGS ARE @ 10 - 25 C GIVESS OTHERWISE SPECIFIED.			
RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	45	Volts
MAXIMUM DC OUTPUT CURRENT (With Cathode Maintained @ T _C = 100 °C)	Io	30	Amps
MAXIMUM NONREPETITIVE FORWARD SURGE CURRENT (t = 8.3ms, Sine)	I _{FSM}	570	Amps
MAXIMUM JUNCTION CAPACITANCE (V _r =5V)	C _T	1600	pF
MAXIMUM THERMAL RESISTANCE (Junction to Mounting Surface, Cathode)	$R_{ heta JC}$	0.50	°C/W
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE	Top/Tstg	-65 to +175	°C

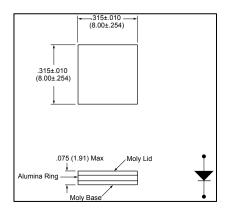
ELECTRICAL CHARACTERISTICS

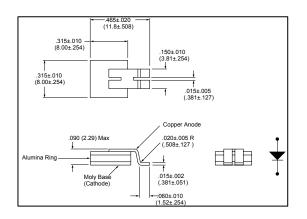
CHARACTERISTIC				
MAXIMUM FORWARD VOLTAGE DROP, Pulsed (I _f = 30 Amps)				
	T _J = 25 °C	V_{f}	0.64	Volts
	T _J = 125 °C		0.57	
MAXIMUM REVERSE CURRENT (I _r @ 45 V PIV)				
	T _J = 25 °C	I _r	0.8	mA
	T _J = 125 °C		30	

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MECHANICAL DIMENSIONS: In Inches / mm

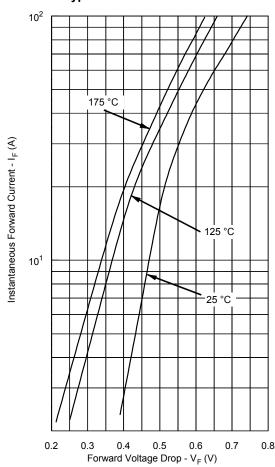
SHD-2



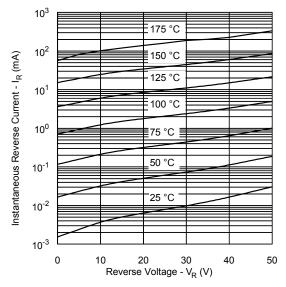


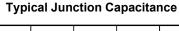
SHD-2B

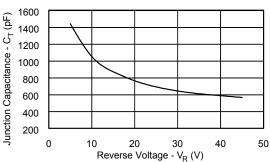
Typical Forward Characteristics



Typical Reverse Characteristics







SHD115422 SHD115422B

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